



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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製品規格/Product Specification 品種名/Type Number: UNR311100 L 1)	DESIGNED	CHECKED	CHECKED	APPROVED

種別/Type	シリコントランジスタ/Silicon Transistors					
用途/Application	デジタル回路用/Digital Circuit					
構造/Structure	PNPエピタキシャルプレーナ形/PNP Epitaxial Planar Type					
外形/Out line	SSSMini3-F1			マーク記号/Marking	6A	
絶対最大定格/ Absolute Maximum Ratings	V _{CB0}	V _{CE0}	I _C	P _T	T _j	T _{stg}
	-50	-50	-100	100	125	-55~+125
	(V)	(V)	(mA)	(mW)	(°C)	(°C)

電気的特性/Electrical characteristics (T_a=25±3°C)

項目/Item	記号/ Symbol	測定条件/Measuring condition	typ.	Limit		Unit
				min.	max.	
コレクタ耐圧 Collector to Base Voltage	V _{CB0}	I _C =-10μA, I _E =0		-50		V
コレクタ耐圧 Collector to Emitter Voltage	V _{CE0}	I _C =-2mA, I _B =0		-50		V
コレクタ遮断電流 Collector Cutoff Current	I _{CB0}	V _{CB} =-50V, I _E =0			-0.1	μA
コレクタ遮断電流 Collector Cutoff Current	I _{CE0}	V _{CE} =-50V, I _B =0			-0.5	μA
エミッタ遮断電流 Emitter Cutoff Current	I _{EB0}	V _{EB} =-6V, I _C =0			-0.5	mA
直流電流増幅率 Collector to Emitter Saturation Voltage	h _{FE}	V _{CE} =-10V, I _C =-5mA		35		-
コレクタ飽和電圧 Collector to Emitter Saturation Voltage	V _{CE(sat)}	I _C =-10mA, I _B =-0.3mA			-0.25	V
ハイレベル出力電圧 Output Voltage High Level	V _{OH}	V _{CC} =-5V, V _B =-0.5V, R _L =1kΩ		-4.9		V
ローレベル出力電圧 Output Voltage Low Level	V _{OL}	V _{CC} =-5V, V _B =-2.5V, R _L =1kΩ			-0.2	V
入力抵抗 Input Resistance	R _I		10	-30%	+30%	kΩ
抵抗比率 Resistance Ratio	R ₁ /R ₂		1.0	0.8	1.2	-
トランジション周波数 Gain Bandwidth Product	f _T	V _{CB} =-10V, I _E =1mA, f=200MHz	80			MHz

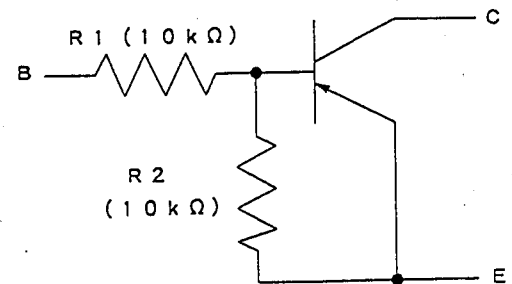
Note: 測定方法は、日本工業規格 JIS C 7030 トランジスタ測定方法による。

Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

1) 包装/Packing

Code	包装形態 /Packing form
L	エンボスTXタイプ/embossed TX type

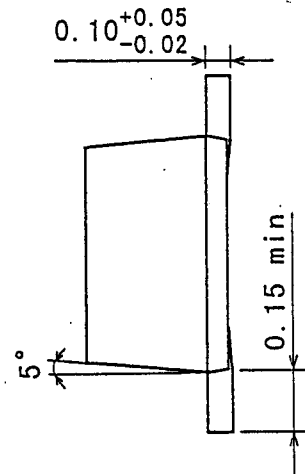
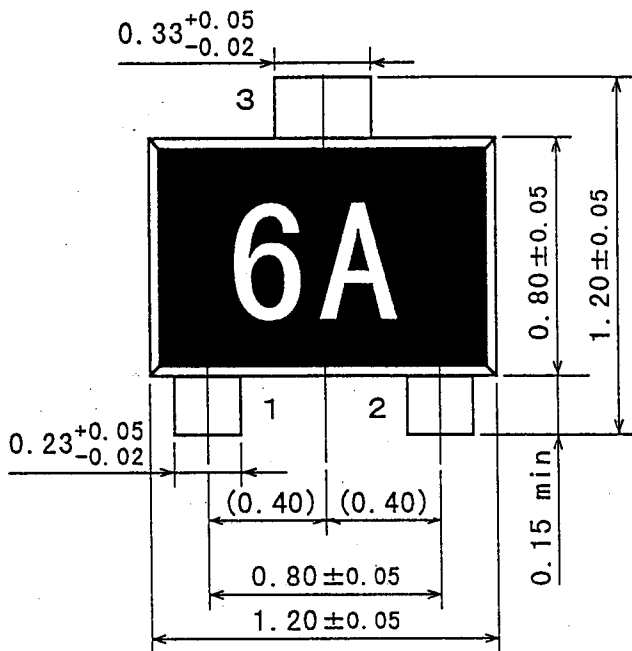
内部接続図/Internally connected circuit



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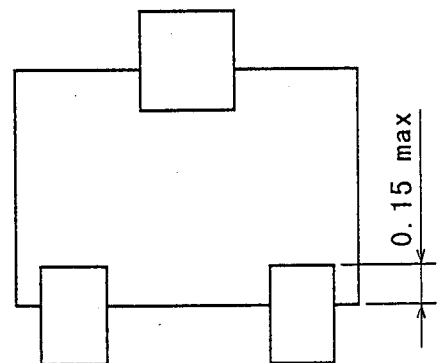
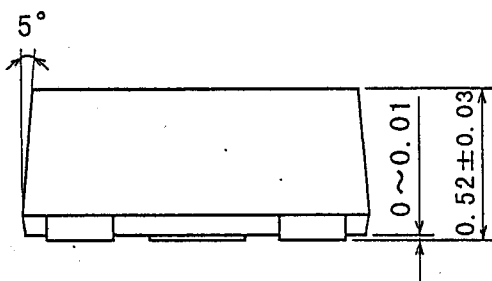
製品規格/Product Specification
 外形図/Out Line
 品種名/Type Number: UNR 3 1 1 1 0 0 L
 1)

単位/Unit : mm



注) 品種略号のみ表示
 Display at trademark

- 1. Base
- 2. Emitter
- 3. Collector



項目/Item	内容/contents
リード材質/Lead Material	銅系/Cu
リード処理/Lead Process	はんだめっき/Solder plating
モールド材質/Mold Material	エポキシ樹脂/Epoxy

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